

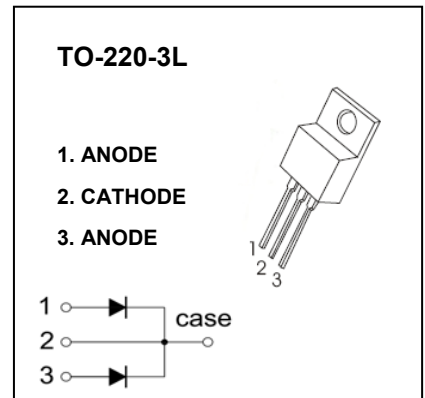
TO-220-3L Plastic-Encapsulate Diodes

MBR1030CT, 35CT, 40CT, 45CT, 50CT, 60CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value						Unit
		MBR 1030CT	MBR 1035CT	MBR 1040CT	MBR 1045CT	MBR 1050CT	MBR 1060CT	
V_{RRM}	Peak repetitive reverse voltage	30	35	40	45	50	60	V
V_{RWM}	Working peak reverse voltage							
V_R	DC blocking voltage							
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	42	V
I_o	Average rectified output current@ $T_c=105^{\circ}\text{C}$	10						A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave	125						A
P_D	Power dissipation	2						W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50						$^{\circ}\text{C}/\text{W}$
T_j	Junction temperature	125						$^{\circ}\text{C}$
T_{stg}	Storage temperature	-55~+150						$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	MBR1030CT	I _R =0.1mA	30			V
		MBR1035CT		35			
		MBR1040CT		40			
		MBR1045CT		45			
		MBR1050CT		50			
		MBR1060CT		60			
Reverse current	I _R	MBR1030CT	V _R =30V			0.1	mA
		MBR1035CT	V _R =35V				
		MBR1040CT	V _R =40V				
		MBR1045CT	V _R =45V				
		MBR1050CT	V _R =50V				
		MBR1060CT	V _R =60V				
Forward voltage	V _{F(1)}	MBR1030CT-1045CT	I _F =5A			0.7	V
		MBR1050CT,1060CT				0.8	
	V _{F(2)} *	MBR1030CT-1045CT	I _F =10A			0.84	
		MBR1050CT,1060CT				0.95	
Typical total capacitance	C _{tot}	MBR1030CT-1060CT	V _R =4V,f=1MHz		150		pF

*Pulse test